

Low Noise Silicon Bipolar RF Transistor

- For low-noise, high gain broadband amplifiers at collector currents from 2 mA to 30 mA
- Pb-free (RoHS compliant) package
- Qualification report according to AEC-Q101 available





ESD (Electrostatic discharge) sensitive device, observe handling precaution!

Туре	Marking	Pin Configuration			Package
BFR93A	R2s	1=B	2=E	3=C	SOT23

Maximum Ratings at T_A = 25 °C, unless otherwise specified

Parameter	Symbol	Value	Unit	
Collector-emitter voltage	$V_{\sf CEO}$	12	V	
Collector-emitter voltage	V_{CES}	20		
Collector-base voltage	V_{CBO}	20		
Emitter-base voltage	V_{EBO}	2		
Collector current	I _C	90	mA	
Base current	I _B	9		
Total power dissipation ¹⁾	P _{tot}	300	mW	
<i>T</i> _S ≤ 111 °C				
Junction temperature	T_{J}	150	°C	
Storage temperature	T_{Stg}	-55 150		

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ²⁾	R _{thJS}	130	K/W

1

 $^{{}^1}T_{
m S}$ is measured on the collector lead at the soldering point to the pcb

 $^{^2}$ For the definition of $R_{th,JS}$ please refer to Application Note AN077 (Thermal Resistance Calculation)



Electrical Characteristics at T_A = 25 °C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	12	-	-	V
$I_{\rm C}$ = 1 mA, $I_{\rm B}$ = 0					
Collector-emitter cutoff current	I _{CES}	-	-	100	μΑ
$V_{CE} = 20 \text{ V}, V_{BE} = 0$					
Collector-base cutoff current	I _{CBO}	-	-	100	nA
$V_{\text{CB}} = 10 \text{ V}, I_{\text{E}} = 0$					
Emitter-base cutoff current	I _{EBO}	-	-	10	μΑ
$V_{\rm EB} = 2.5 \rm V, I_{\rm C} = 0$					
DC current gain	h _{FE}	70	100	140	-
$I_{\rm C}$ = 30 mA, $V_{\rm CE}$ = 8 V, pulse measured					



Electrical Characteristics at T_{Δ} = 25 °C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics (verified by random sampling	ng)	1		Ī	1
Transition frequency	f_{T}	4.5	6	-	GHz
$I_{\rm C}$ = 30 mA, $V_{\rm CE}$ = 8 V, f = 500 MHz					
Collector-base capacitance	C _{cb}	-	0.54	0.8	pF
$V_{\text{CB}} = 10 \text{ V}, f = 1 \text{ MHz}, V_{\text{BE}} = 0$,					
emitter grounded					
Collector emitter capacitance	C _{ce}	-	0.25	-	
$V_{CE} = 10 \text{ V}, f = 1 \text{ MHz}, V_{BE} = 0$,					
base grounded					
Emitter-base capacitance	C _{eb}	-	1.9	-	
$V_{\text{EB}} = 0.5 \text{ V}, f = 1 \text{ MHz}, V_{\text{CB}} = 0$,					
collector grounded					
Minimum noise figure	NF _{min}				dB
$I_{\rm C}$ = 5 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$,					
f = 900 MHz		-	1.5	-	
f = 1.8 GHz		-	2.6	-	
Power gain, maximum available ¹⁾	G _{ma}				
$I_{\rm C}$ = 30 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm Sopt}$, $Z_{\rm L}$ = $Z_{\rm Lopt}$,					
f = 900 MHz		_	14.5	-	
f = 1.8 GHz		-	9.5	-	
Transducer gain	$ S_{21e} ^2$				dB
$I_{\rm C}$ = 30 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm L}$ = 50 Ω ,					
f = 900 MHz		-	12.5	-	
f = 1.8 MHz		-	7	-	
Third order intercept point at output ²⁾	IP ₃	-	15	-	dBm
$I_{\rm C}$ = 30mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm L}$ = 50 Ω ,					
f = 900 MHz					
1dB Compression point	P _{-1dB}	_	6	-	
	100				
$I_{\rm C}$ = 30 mA, $V_{\rm CE}$ = 8 V, $Z_{\rm S}$ = $Z_{\rm L}$ = 50 Ω ,					

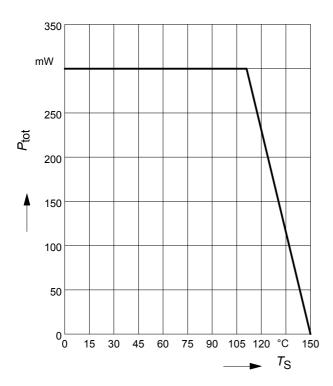
 $^{{}^{1}}G_{\text{ma}} = |S_{21e} / S_{12e}| (k-(k^{2}-1)^{1/2})$

²IP3 value depends on termination of all intermodulation frequency components.

Termination used for this measurement is 50Ω from 0.2 MHz to 12 GHz



Total power dissipation $P_{tot} = f(T_S)$

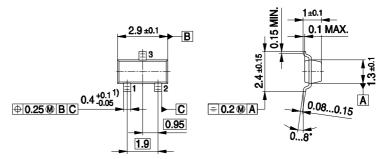


4



Package Outline

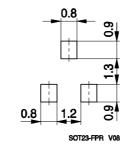




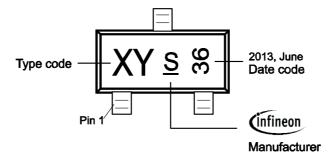
1) Lead width can be 0.6 max. in dambar area

SOT23-PO V08

Foot Print

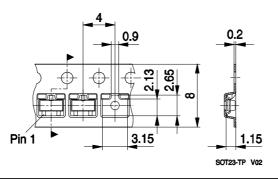


Marking Layout



Standard Packing

Reel o 180 mm: 3.000 Pieces / Reel Reel o 330 mm = 10.000 Pieces / Reel





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6

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